DATA SHEET

BFS17
NPN 1 GHz wideband transistor

Product specification
File under Discrete Semiconductors, SC14

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Philips
Semiconductors

PHILIPS

NPN 1 GHz wideband transistor BFS17

DESCRIPTION

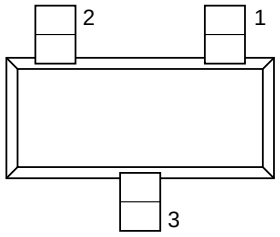
NPN transistor in a plastic SOT23 package.

APPLICATIONS

- A wide range of RF applications such as:
  - Mixers and oscillators in TV tuners
  - RF communications equipment.

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



Top view

Marking code: E1p.

Fig.1 SOT23.

QUICK REFERENCED DATA

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	25	V
V_{CEO}	collector-emitter voltage	open base	–	15	V
I_C	DC collector current		–	25	mA
P_{tot}	total power dissipation	up to T_s = 70 °C; note 1	–	300	mW
f_T	transition frequency	I_C = 25 mA; V_{CE} = 5 V; f = 500 MHz; T_j = 25 °C	1	–	GHz
F	noise figure	I_C = 2 mA; V_{CE} = 5 V; R_S = 50 Ω; f = 500 MHz; T_j = 25 °C	4.5	–	dB

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	25	V
V_{CEO}	collector-emitter voltage	open base	–	15	V
V_{EBO}	emitter-base voltage	open collector	–	2.5	V
I_C	DC collector current		–	25	mA
I_{CM}	peak collector current		–	50	mA
P_{tot}	total power dissipation	up to T_s = 70 °C; note 1	–	300	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C

Note to the Quick reference data and the Limiting values

1. T_s is the temperature at the soldering point of the collector pin.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j\text{-}s}$	thermal resistance from junction to soldering point	up to T_s = 70 °C; note 1	260	K/W

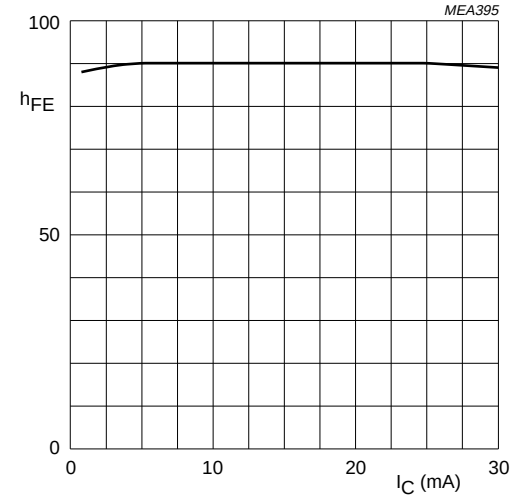
Note

1. T_s is the temperature at the soldering point of the collector pin.

CHARACTERISTICS

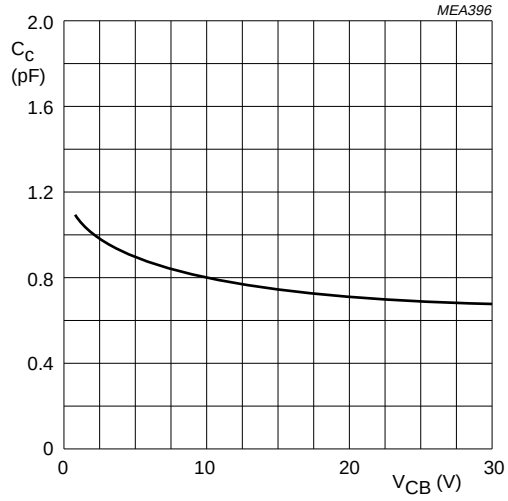
T_j = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector cut-off current	I_E = 0; V_{CB} = 10 V	–	–	10	nA
h_{FE}	DC current gain	I_C = 2 mA; V_{CE} = 1 V	25	90	–	
		I_C = 25 mA; V_{CE} = 1 V	25	90	–	
f_T	transition frequency	I_C = 2 mA; V_{CE} = 5 V; f = 500 MHz	–	1	–	GHz
		I_C = 25 mA; V_{CE} = 5 V; f = 500 MHz	–	1.6	–	GHz
C_c	collector capacitance	$I_E = i_e$ = 0; V_{CB} = 10 V; f = 1 MHz	–	0.8	1.5	pF
C_e	emitter capacitance	$I_C = i_c$ = 0; V_{EB} = 0.5 V; f = 1 MHz	–	–	2	pF
C_{re}	feedback capacitance	I_C = 1 mA; V_{CE} = 5 V; f = 1 MHz	–	0.65	–	pF
F	noise figure	I_C = 2 mA; V_{CE} = 5 V; R_S = 50 Ω; f = 500 MHz	–	4.5	–	dB



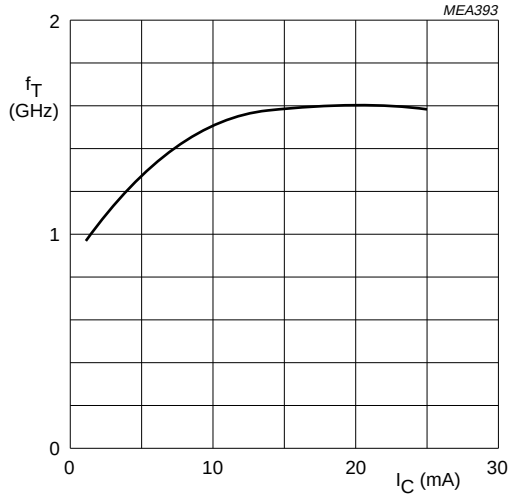
V_{CE} = 1 V; T_j = 25 °C.

Fig.2 DC current gain as a function of collector current.



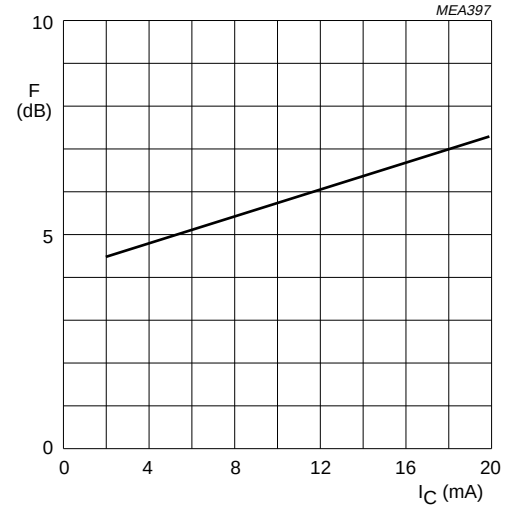
$I_E = i_e$ = 0; f = 1 MHz; T_j = 25 °C.

Fig.3 Collector capacitance as a function of collector-base voltage.



V_{CE} = 5 V; f = 500 MHz; T_j = 25 °C.

Fig.4 Transition frequency as a function of collector current.

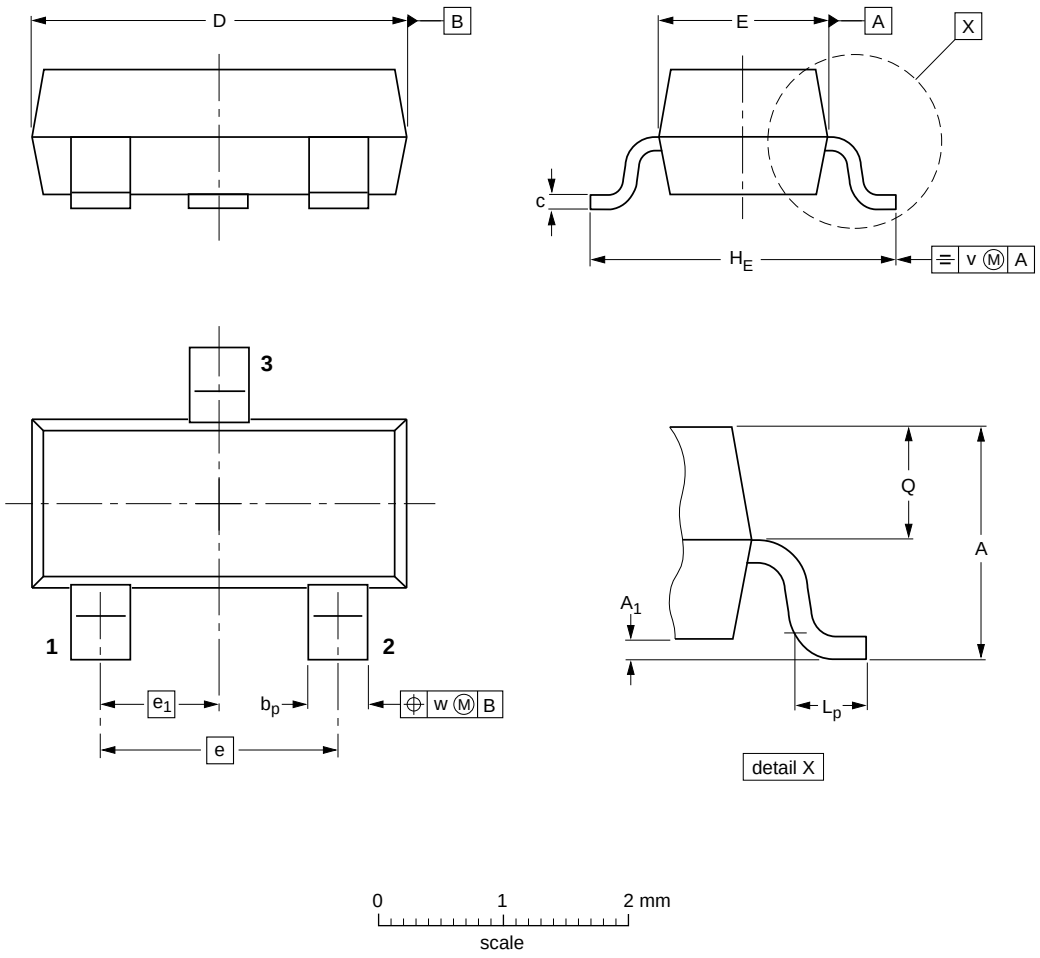


V_{CE} = 5 V; R_S = 50 Ω; f = 500 MHz; T_j = 25 °C.

Fig.5 Minimum noise figure as a function of collector current.

PACKAGE OUTLINE

Package description **SOT23**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1 max.	b_p	c	D	E	e	e_1	H_E	L_p	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT23						96-10-18

DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.